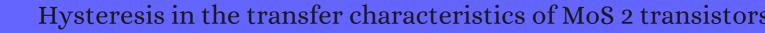
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DOI: 10.1088/2053-1583/aa91a7 2D Materials, 2018, 5, 015014.

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#	Paper	IF	Citations
177	Novel circuit design for high-impedance and non-local electrical measurements of two-dimensional materials. <b>2018</b> , 89, 024705		1
176	Quantitative analysis of trap states through the behavior of the sulfur ions in MoS2FETs following high vacuum annealing. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 105102	3	4
175	Highly sensitive MoS photodetectors with graphene contacts. <i>Nanotechnology</i> , <b>2018</b> , 29, 20LT01	3.4	25
174	P-Type Doping of WS2 Quantum Dots via Pulsed Laser Ablation. <b>2018</b> , 5, 4828-4837		9
173	Environmental Effects on the Electrical Characteristics of Back-Gated WSelField-Effect Transistors. <i>Nanomaterials</i> , <b>2018</b> , 8,	5.4	38
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170	Gas adsorbates are Coulomb scatterers, rather than neutral ones, in a monolayer MoS field effect transistor. <i>Nanoscale</i> , <b>2018</b> , 10, 10856-10862	7.7	6
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167	Bipolar resistive switching behavior in MoS2 nanosheets fabricated on ferromagnetic shape memory alloy. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 262106	3.4	27
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